

# NIKKO

# PRE-AMP

# BETA 20

## STEREO PRE-AMPLIFIER



### TYPE AND VOLTAGE

|                 |                 |         |
|-----------------|-----------------|---------|
| <b>W-TYPE:</b>  | UL and CSA type | 120V AC |
| <b>E -TYPE:</b> | NK-STD type     | 220V AC |
| <b>B -TYPE:</b> | BS type         | 240V AC |

# SERVICE MANUAL

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# SPECIFICATIONS

## Pre Amplifier Section

Total Harmonic Distortion (20 to 20,000 Hz),  
 Phono (MC) to Tape Out (at 4 V output)  
 ..... no more than 0.004 %  
 Phono (MM) to Tape Out (at 4 V output)  
 ..... no more than 0.004 %  
 Aux to Pre Out (at 4 V output)  
 ..... no more than 0.007 %

Input Sensitivity (1000 Hz, 1 V output),  
 Phono (MC): ..... 0.2 mV  $\pm$  2 dB  
 Phono (MM): ..... 2.0 mV  $\pm$  2 dB  
 Tuner: ..... 110 mV  $\pm$  2 dB  
 Aux: ..... 110 mV  $\pm$  2 dB  
 Tape 1, 2: ..... 110 mV  $\pm$  2 dB

Input Impedance (1000 Hz),  
 Phono (MC): ..... 100  $\pm$  10 ohms  
 Phono (MM): ..... 47  $\pm$  5 kohms  
 Aux: ..... 47  $\pm$  5 kohms  
 Tape 1, 2: ..... 47  $\pm$  5 kohms

Maximum Input Signal (1000 Hz, 0.1 % THD),  
 Phono (MC): ..... more than 25 mV  
 Phono (MM): ..... more than 250 mV

## General

Power Requirement,  
 U. S. A. & Canada model: ..... AC 120V/60 Hz  
 European model: ..... AC 220V/50 Hz  
 U. K. model: ..... AC 240V/50 Hz  
 Power Consumption: ..... 18 watts

Output Level (1000 Hz),  
 Tape Out: ..... 110 mV  $\pm$  2 dB  
 Pre Out: ..... 1000 mV  $\pm$  2 dB

Signal to Noise Ratio with IHF-A Network,  
 Phono (MC): ..... more than 67 dB  
 Phono (MM): ..... more than 80 dB  
 Tuner: ..... more than 95 dB  
 Aux: ..... more than 95 dB  
 Tape In 1, 2: ..... more than 95 dB

Frequency Response (10 ~ 100,000 Hz),  
 Tuner: ..... +0, -1 dB  
 Aux: ..... +0, -1 dB  
 Tape In 1, 2: ..... +0, -1 dB

RIAA Equalization Deviation (20 ~ 20,000 Hz),  
 Phono (MM) to Tape Out: .....  $\pm$ 0.5 dB

Tone Controls,  
 Bass (70 Hz): .....  $\pm$ 8 dB  
 Treble (10,000 Hz): .....  $\pm$ 8 dB

Subsonic Filter: ..... 15 Hz, 12 dB/oct.  
 Mute Time: ..... 7  $\pm$  2 seconds

Dimensions,  
 Width: ..... 482 mm, 19 inches  
 Height: ..... 70 mm, 2-3/4 inches  
 Depth: ..... 330 mm, 13 inches

Weight,  
 Without package: ..... 5.2 kg, 11.4 lbs  
 With package: ..... 6.6 kg, 14.5 lbs

\* Specifications are subject to change without notice.

# BLOCK DIAGRAM

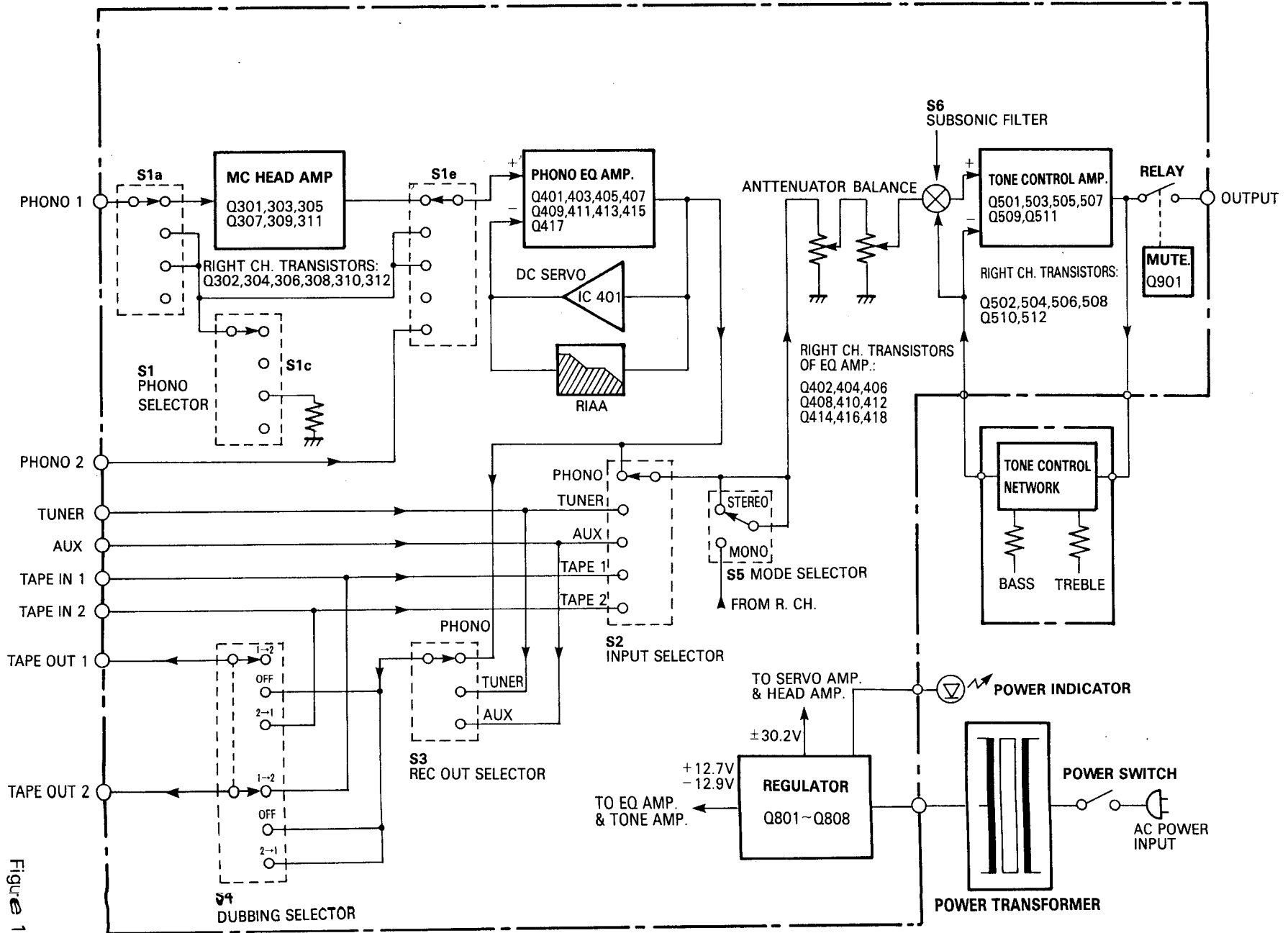


Figure 1

# DISASSEMBLY

## 1. CABINET COVER REMOVAL

- a. Remove four tapping screws from the top of the metal cover.
- b. Remove four screws from both sides of the metal cover.
- c. Lift the cabinet cover away from the unit.

## 2. BOTTOM PLATE REMOVAL

- a. Remove eight tapping screws (#1 ~ #8) as shown in Photo 1.

## 3. FRONT PANEL REMOVAL

- a. Remove two knobs (#1 and #2) (Photo 2) from the front panel by pulling them forward.
- b. Using a hexagonal wrench, remove five knobs (#3 ~ #7) as shown in Photo 2.
- c. Remove two nuts (#8 and #9) (Photo 2) and lift out the front panel.

## 4. POWER TRANSFORMER REMOVAL

- a. Disconnect all wires from the power transformer.
- b. Remove two screws (#10 and #11) (photo 2) and lift the power transformer up and out of chassis.

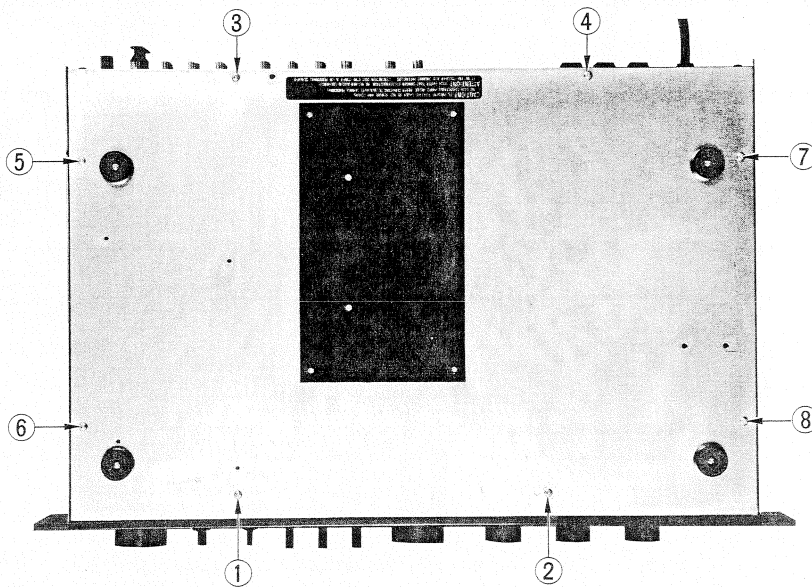


Photo 1

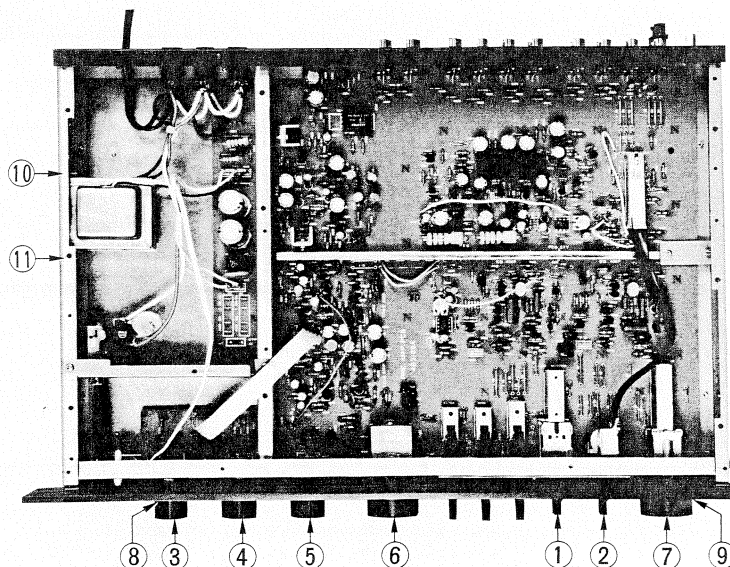


Photo 2

# ALIGNMENT

## GENERAL ALIGNMENT INSTRUCTIONS

1. Allow a minimum of 10 minutes warm-up for the unit.
2. When adjusting, voltmeter's needle may swing backward. In this case, simply reverse the voltmeter connection.

## DC BALANCE ADJUSTMENT (EQ AMP SECTION)

1. Set the Phono Selector Switch to "PHONO 1 47 kohm" position.
2. Insert short-pin-plugs to the PHONO 1 input terminals on the rear panel.
3. Connect a DC voltmeter to the test points marked "TP" on the Pre Amp PC Board. (refer to Photo 3)
4. Adjust the potentiometer R455 (left channel) or R456 (right channel) so that the DC voltmeter indicates  $0 \pm 1$  mV.

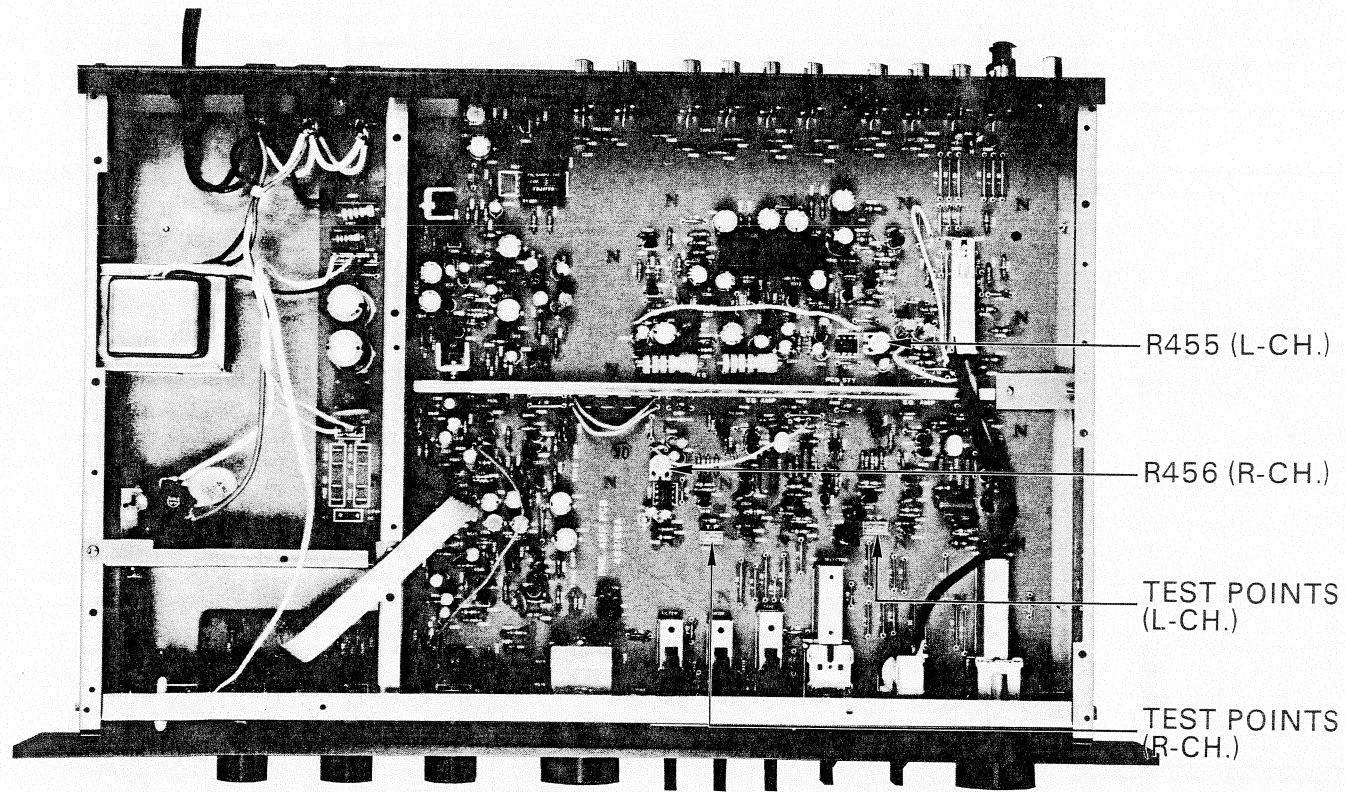



Photo 3

# PARTS LOCATION

NOTE: Numbers of three digits with a  are related to the KEY NUMBER on parts list.

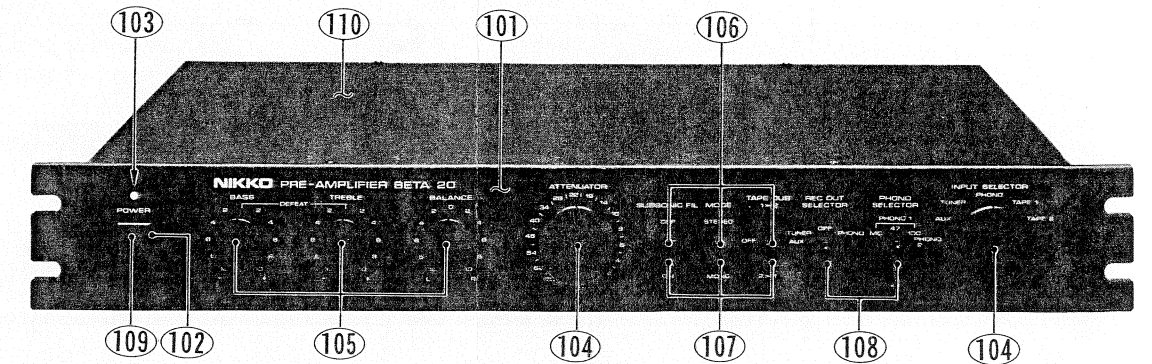


Photo 4

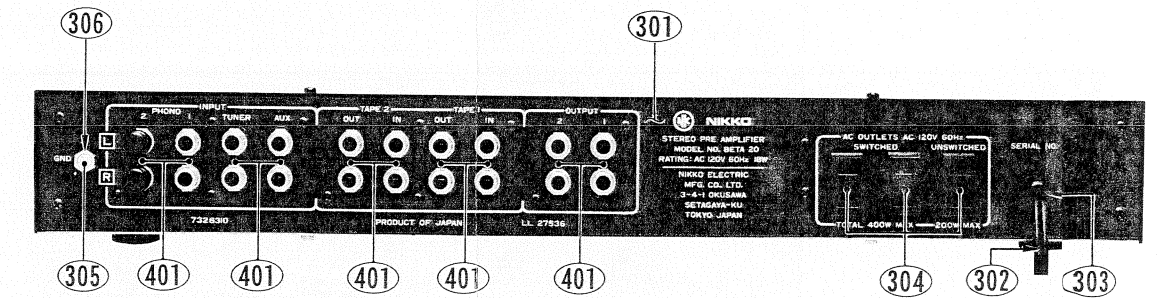


Photo 5

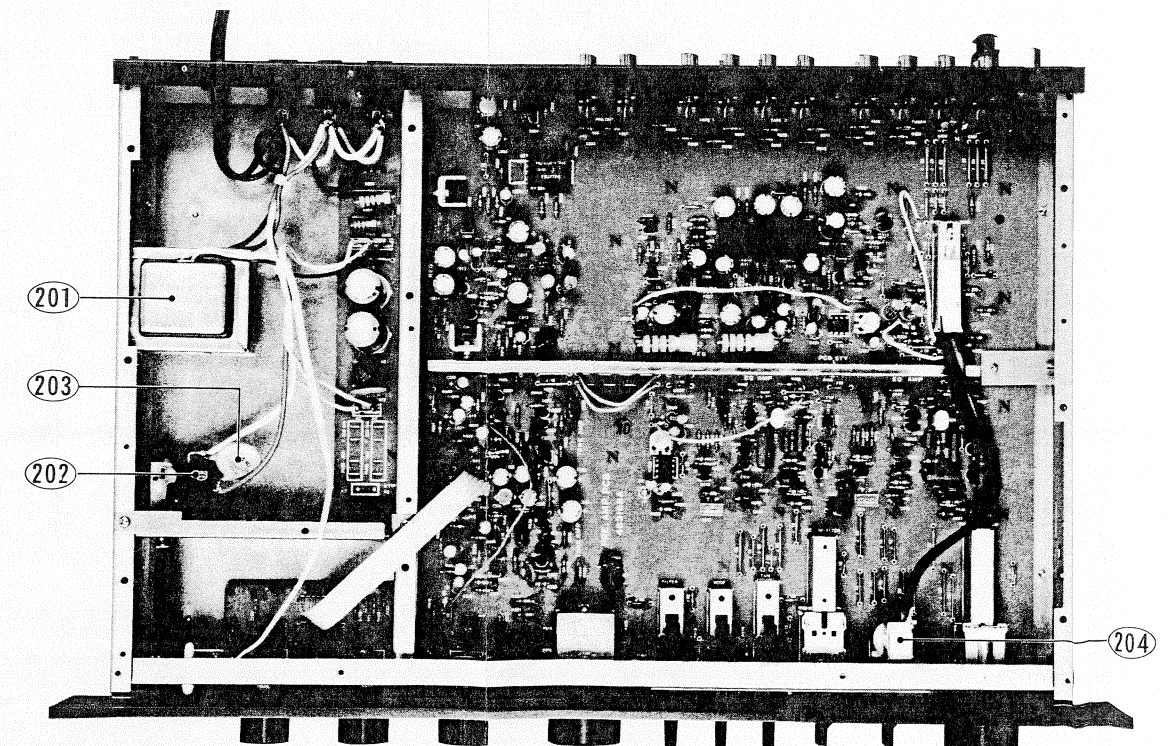
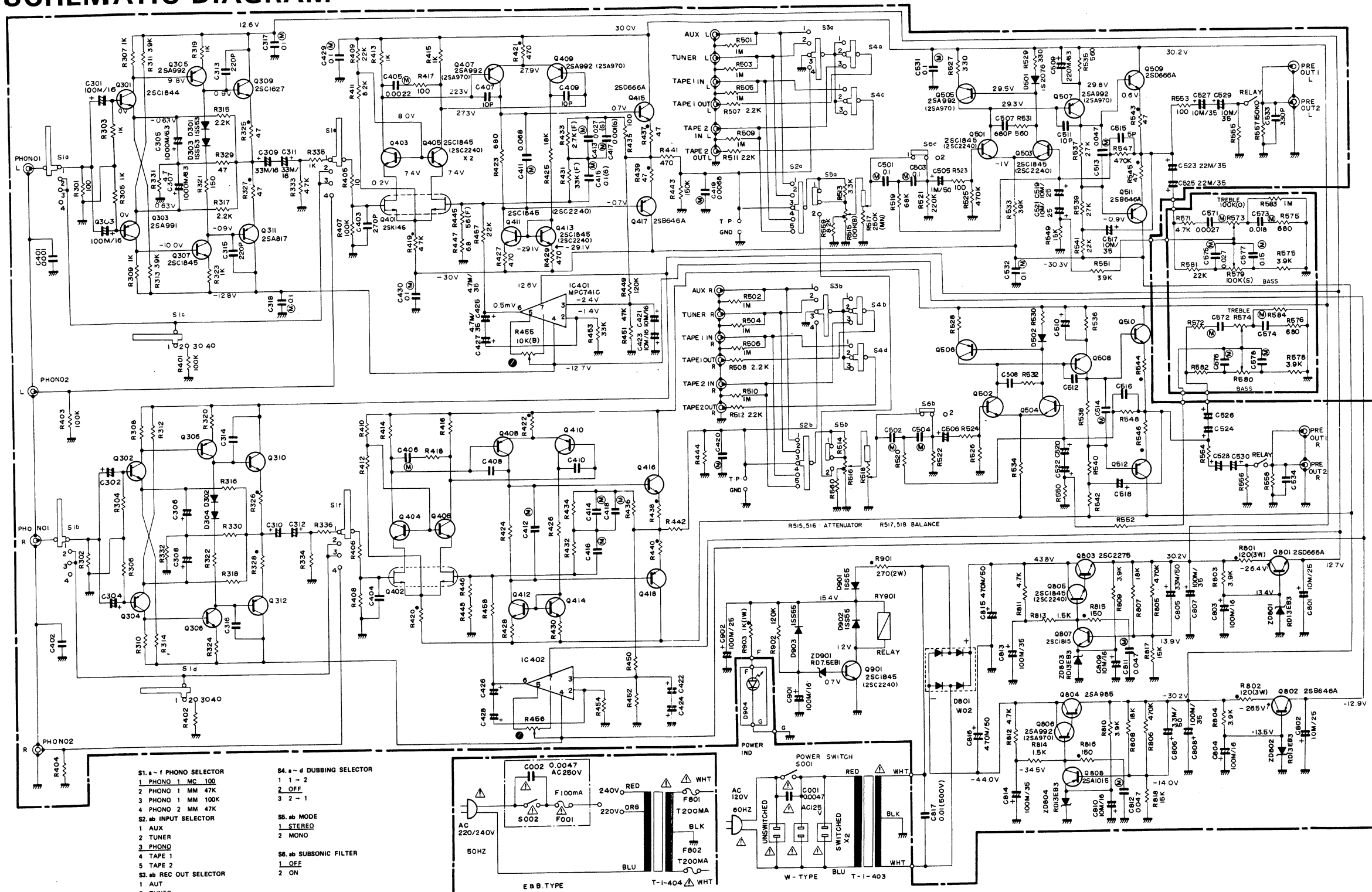


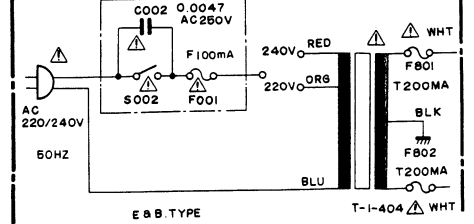
Photo 6



# SCHEMATIC DIAGRAM



- S1, s - PHONO SELECTOR**  
 1 PHONO 1 MC 100  
 2 PHONO 1 MM 47K  
 3 PHONO 1 MM 100K  
 4 PHONO 2 MM 47K  
**S2, sb INPUT SELECTOR**  
 1 AUX  
 2 TUNER  
 3 PHONO  
 4 TAPE 1  
 5 TAPE 2  
**S3, sb REC OUT SELECTOR**  
 1 AUX  
 2 TUNER  
 3 OFF  
 4 PHONO
- S4, s - d DUBBING SELECTOR**  
 1 1 - 2  
 2 OFF  
 3 2 - 1
- S5, sb MODE**  
 1 STEREO  
 2 MONO
- S6, sb SUBSONIC FILTER**  
 1 OFF  
 2 ON



- NOTES:**  
 1. SCHEMATIC IS SUBJECT TO CHANGE WITHOUT NOTICE.  
 2. RESISTANCE VALUES ARE IN OHMS. K = 1,000; M = 1,000,000.  
 3. CAPACITANCE VALUES 1.0 AND ABOVE ARE IN pF OR μF (P = pF, M = μF). LESS THAN 1.0 ARE IN μF. (ELECTROLYTIC CAPACITANCE VALUES ARE IN μF/MV.)  
 4. VOLTAGES ARE MEASURED TO CHASSIS GROUND WITH A "DC VOLTMETER".

- SCHEMATIC SYMBOLS:**  
 POLYESTER FILM CAPACITOR  
 NONFLAMMABLE RESISTOR

**WARNING:**  
 Δ INDICATES SAFETY CRITICAL COMPONENTS.  
 FOR CONTINUED SAFETY, REPLACE SAFETY CRITICAL COMPONENTS ONLY WITH MANUFACTURER'S RECOMMENDED PARTS.

**SEMICONDUCTORS**

|  |  |
|--|--|
|  | 2S1817<br>2S1970<br>2S1991<br>2S1992<br>2S1015<br>2S1627<br>2S1815<br>2S1844<br>2S1845<br>2S2240<br>2S664A |
|  | 2S1815<br>2S1844<br>2S1845<br>2S2240<br>2S664A   |
|  | 2S1815<br>2S1844<br>2S1845<br>2S2240<br>2S664A   |
|  | 2S1815<br>2S1844<br>2S1845<br>2S2240<br>2S664A   |

# P.C. BOARD (BOTTOM VIEW)

## PRE-AMP PCB

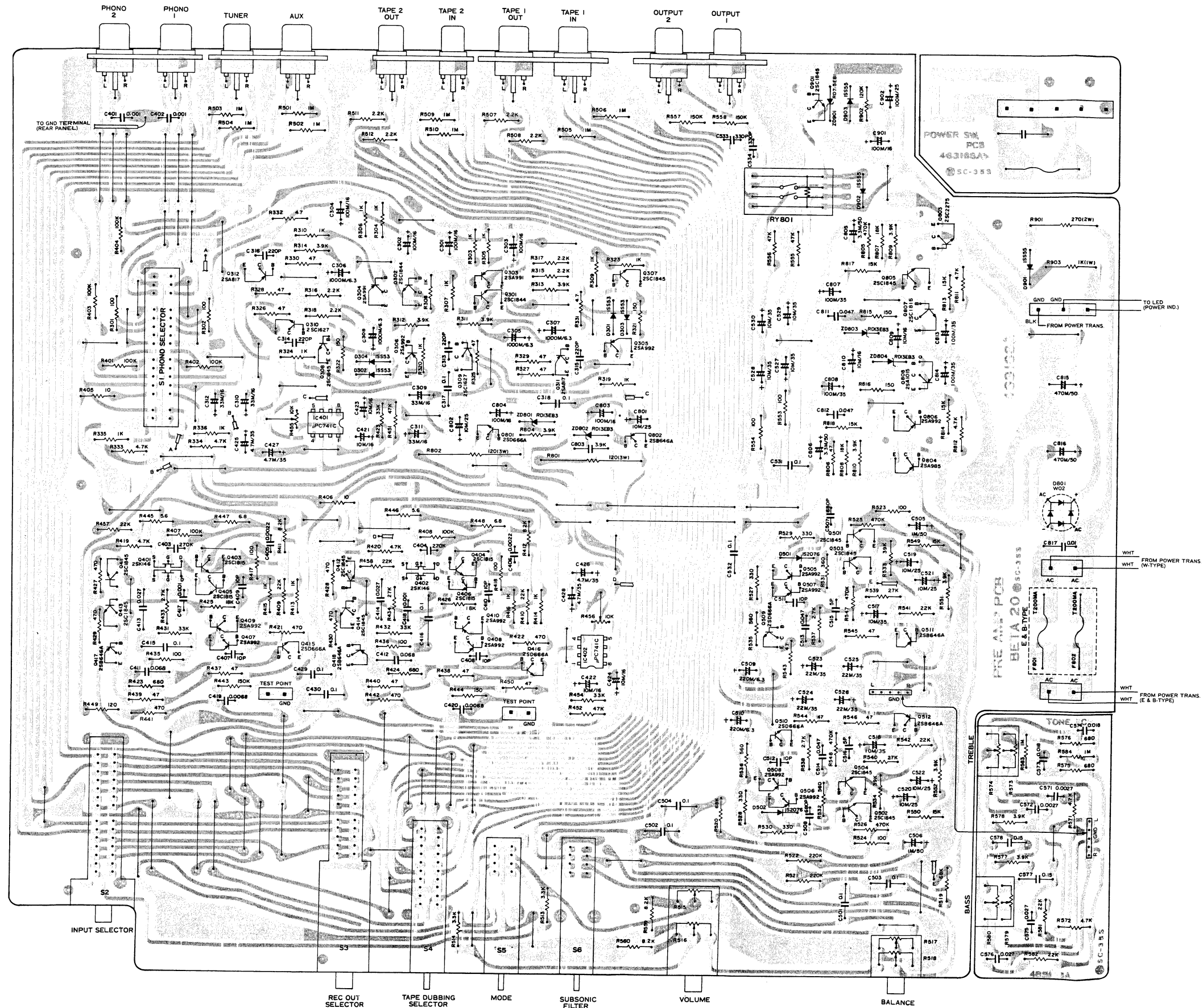


Figure 3





**PART ORDERING PROCEDURE** ----- DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER: (these are control # for the factory only.) Include in any order: a. Part number, b. Part description, c. Model number. (any of the above lacking from an order may delay shipment of the order.)

| KEY NO.                       | SYMBOL NO. | TYPE <sup>+</sup> WEB | DESCRIPTION <sup>++</sup>        | PART NO. |
|-------------------------------|------------|-----------------------|----------------------------------|----------|
| <b>(TONE CONTROL SECTION)</b> |            |                       |                                  |          |
| R573,574                      | 1 1 1      | VR                    | GM70EE71C - 100kohm x 2 - treble | 4321140  |
| R579,580                      | 1 1 1      | VR                    | GM70EE72C - 100kohm x 2 - bass   | 4321150  |
| C571,572                      | 2 2 2      | M-CAP                 | 0.0027μf 10% 50V                 | 222272K  |
| C573,574                      | 2 2 2      | M-CAP                 | 0.018μf 10% 50V                  | 222183K  |
| C574,576                      | 2 2 2      | M-CAP                 | 0.027μf 10% 50V                  | 222273K  |
| C577,578                      | 2 2 2      | M-CAP                 | 0.15μf 10% 50V                   | 222154K  |
| R571,572                      | 2 2 2      | RES                   | 4.7kohm 5% ¼W                    | 328472J  |
| R575,576                      | 2 2 2      | RES                   | 680ohm 5% ¼W                     | 328681J  |
| R577,578                      | 2 2 2      | RES                   | 3.9kohm 5% ¼W                    | 328392J  |
| R581,582                      | 2 2 2      | RES                   | 22kohm 5% ¼W                     | 328223J  |
| R583,584                      | 2 2 2      | RES                   | 1 meg.ohm 5% ¼W                  | 328105J  |

| KEY NO.                          | SYMBOL NO. | TYPE <sup>+</sup> WEB | DESCRIPTION <sup>++</sup> | PART NO. |
|----------------------------------|------------|-----------------------|---------------------------|----------|
| <b>(POWER SWITCH SECTION)</b>    |            |                       |                           |          |
| SW2                              | - 1 1      | Switch, push          | ESB-70823S - power        | 4041600  |
| C002                             | - 1 1      | M-CAP                 | 0.0047μf AC250V           | 283472M  |
| F001                             | - 1 1      | Midget fuse           | T100MA 250V               | 4720430  |
| <b>(POWER INDICATOR SECTION)</b> |            |                       |                           |          |
| D904                             | 1 1 1      | LED                   | BR5504S                   | 5060300  |
|                                  | 1 1 1      | Spacer, LED           |                           | 7903110  |

# SEMICONDUCTOR DATA

## TRANSISTORS

† NOTES Ge: Germanium A : Alloy Df: Drift-field M : Mesa  
 Si: Silicon B : Base E : Epitaxial P : Planer  
 D : Diffused G : Grown Pc : Point-contact  
 Dd : Double-diffused J : Junction Td : Triple-diffused

| DEVICE TYPE     | APPLICATIONS  | STRUCTURE† | MAXIMUM RATINGS Absolute-Maximum Values:<br>(T <sub>A</sub> = 25°C unless otherwise specified) |  |                                       |   |  | ELECTRICAL CHARACTERISTICS Typical Values: (T <sub>A</sub> = 25°C unless otherwise specified) |                     |                 |                     |                     |                          |                     |                     |                      |                      |                     |   |                          |         | MANUFACTURER |
|-----------------|---------------|------------|--|--|---------------------------------------|---|--|---|---------------------|-----------------|---------------------|---------------------|--------------------------|---------------------|---------------------|----------------------|----------------------|---------------------|---|--------------------------|---------|--------------|
|                 |               |            | Collector-to-Base Voltage V <sub>CB0</sub> (V)   | Emitter-to-Base Voltage V <sub>EB0</sub> (V) | Collector Current I <sub>C</sub> (mA) | Collector Dissipation P <sub>C</sub> (mW) | Junction Temperature T <sub>J</sub> (°C) | Collector Cutoff Current I <sub>CB0</sub> (μA)  | V <sub>CB</sub> (V) | h <sub>FE</sub> | V <sub>CE</sub> (V) | I <sub>C</sub> (mA) | V <sub>CE(sat)</sub> (V) | I <sub>C</sub> (mA) | I <sub>B</sub> (mA) | f <sub>T</sub> (MHz) | V <sub>CE*</sub> (V) | I <sub>E</sub> (mA) | Output Capacitance C <sub>ob</sub> (pF) | Others                   |         |              |
| 2SA817 (Y)      | AF, Driver    | PNP Si-E   | -80  | -5   | -300                                  | 600                                       | 150                                      | -0.1 max.   | -50                 | 120 ~ 240       | -2                  | 50                  | -0.4 max.                | -200                | -20                 | 100                  | -10                  | -10*                | 14                                      | Complementary to 2SC1627 | TOSHIBA |              |
| 2SA991 (E, F)   | AF, Low noise | PNP Si-E   | -80  | -5   | -100                                  | 500                                       | 125                                      | -0.05 max.  | -60                 | 300 ~ 800       | -6                  | -0.1                | -0.5 max.                | -100                | -10                 | 90                   | -6                   | 1                   | 10 max.                                 | Complementary to 2SC1844 | NEC     |              |
| 2SA992 (E, F)   | AF, Low noise | PNP Si-E   | -120   | -5   | -50                                   | 500                                       | 125                                      | -0.05 max.  | -120                | 300 ~ 800       | -6                  | -0.1                | -0.3 max.                | -10                 | -1                  | 100                  | -6                   | 1                   | 3 max.                                  | Complementary to 2SC1845 | NEC     |              |
| 2SA985 (P, Q)   | AF, Power amp | PNP Si-E   | -120   | -5   | -1.5A                                 | 25W (T <sub>C</sub> = 25°C)               | 150                                      | -1 max.   | -120                | 100 ~ 320       | -5                  | -300                | -2 max.                  | -1A                 | -100                | 180                  | -5                   | -200*               | 29                                      | Complementary to 2SC2275 | NEC     |              |
| 2SA1015 (Y, GR) | AF, General   | PNP Si-E   | -50  | -5   | -150                                  | 400                                       | 125                                      | -0.1 max.   | -50                 | 120 ~ 400       | -6                  | -2                  | -0.3 max.                | -100                | -10                 | 80 min.              | -10                  | -1*                 | 7 max.                                  | Complementary to 2SC1815 | TOSHIBA |              |
| 2SB646A (B, C)  | AF, Driver    | PNP Si-E   | -120   | -5   | -50                                   | 900                                       | 150                                      | -10 max.  | -100                | 60 ~ 200        | -5                  | -10                 | -2 max.                  | -30                 | -3                  | 140                  | -5                   | -10*                | 4                                       | Complementary to 2SD666A | HITACHI |              |
| 2SC1627 (Y)     | AF, Driver    | NPN Si-E   | 80   | 5  | 300                                   | 600                                       | 150                                      | 0.1 max.  | 50                  | 120 ~ 240       | 2                   | 50                  | 0.5 max.                 | 200                 | 10                  | 100                  | 10                   | 10*                 | 10                                      | Complementary to 2SA817  | TOSHIBA |              |
| 2SC1815 (Y, GR) | AF, General   | NPN Si-E   | 60   | 5  | 150                                   | 400                                       | 125                                      | 0.1 max.  | 60                  | 120 ~ 400       | 6                   | 2                   | 0.25 max.                | 100                 | 10                  | 80 min.              | 10                   | 1*                  | 3 max.                                  | Complementary to 2SA1015 | TOSHIBA |              |
| 2SC1844 (E, F)  | AF, Low noise | NPN Si-E   | 60   | 5  | 100                                   | 500                                       | 125                                      | 0.05 max.   | 60                  | 300 ~ 800       | 6                   | 1                   | 0.3 max.                 | 100                 | -10                 | 100                  | 6                    | -1                  | 8 max.                                  | Complementary to 2SA991  | NEC     |              |
| 2SC1845 (E, F)  | AF, Low noise | NPN Si-E   | 120  | 5  | 50                                    | 500                                       | 125                                      | 0.05 max.   | 120                 | 300 ~ 800       | 6                   | 1                   | 0.3 max.                 | 10                  | 1                   | 110                  | 6                    | -1                  | 2.5 max.                                | Complementary to 2SA992  | NEC     |              |
| 2SC2275 (P, Q)  | AF, Power amp | NPN Si-E   | 120  | 5  | 1.5A                                  | 25W (T <sub>C</sub> = 25°C)               | 150                                      | 1 max.  | 120                 | 100 ~ 320       | 5                   | 300                 | 2 max.                   | 1A                  | 100                 | 200                  | 5                    | 200*                | 19                                      | Complementary to 2SA985  | NEC     |              |
| 2SD666A (B, C)  | AF, Driver    | NPN Si-E   | 120  | 5  | 50                                    | 900                                       | 150                                      | 10 max.   | 100                 | 60 ~ 200        | 5                   | 10                  | 2 max.                   | 30                  | 3                   | 140                  | 5                    | 10*                 | 3                                       | Complementary to 2SB646A | HITACHI |              |

## FIELD EFFECT TRANSISTOR

| DEVICE TYPE | APPLICATIONS                   | STRUCTURE†                   | MAXIMUM RATINGS Absolute-Maximum Values:<br>(T <sub>A</sub> = 25°C unless otherwise specified) |   |                                  |                                   |                                       |  |   | ELECTRICAL CHARACTERISTICS Typical Values: (T <sub>A</sub> = 25°C unless otherwise specified) |   |                         |   |           |  |                           |  |                        |   |                       |  |  |                                | MANUFACTURER |
|-------------|--------------------------------|------------------------------|--|---|----------------------------------|-----------------------------------|---------------------------------------|--|---|---|---|-------------------------|---|-----------|--|---------------------------|--|------------------------|---|-----------------------|--|--|--------------------------------|--------------|
|             |                                |                              | Gate-to-Drain Voltage V <sub>GD0</sub> (V)   | Gate-to-Source Voltage V <sub>GS0</sub> (V) | Gate Current I <sub>G</sub> (mA) | Drain Current I <sub>D</sub> (mA) | Total Dissipation P <sub>D</sub> (mW) | Channel Temperature T <sub>ch</sub> (°C) | Gate Leak Current (Test Conditions)           | IGSS (nA)   | Gate to Drain Breakdown Voltage (Test Conditions) | V <sub>BR</sub> GDO (V) | Drain Current (Test Conditions)   | IDSS (mA) | Gate to Source Cutoff Voltage (Test Conditions)                        | V <sub>GS</sub> (off) (V) | Forward Transfer Admittance (Test Conditions)            | Y <sub>fs</sub>   (mg) | Feed Back Capacitance (Test Conditions) | C <sub>rss</sub> (pF) | Power Gain (Common Source) (Test Conditions) | GPS (dB)   | Noise Figure (Test Conditions) |              |
| 2SK146 (GR) | AF, Low noise Differential amp | Si N-channel junction (Dual) | -40  |   | 10                               |                                   | 800/unit                              | 125                                      | V <sub>GS</sub> = -30V<br>V <sub>DS</sub> = 0 | -1  | V <sub>DS</sub> IG = -100μA                       | -40 min.                | V <sub>DS</sub> = 10V<br>I <sub>DSS</sub> = 5 ~ 10<br>V <sub>GS</sub> = 0 |           | V <sub>GS</sub> = 10V<br>I <sub>DSS</sub> = 8mA<br>V <sub>GS</sub> = 0 | 48                        | V <sub>DS</sub> = 10V<br>I <sub>D</sub> = 0<br>f = 1 MHz | 15                     |   |                       |  | V <sub>DS</sub> = 10V<br>I <sub>D</sub> = 5mA<br>f = 1 kHz | 1                              | TOSHIBA      |

## DIODES, LED'S

| DEVICE TYPE | APPLICATIONS           | STRUCTURE†     | MAXIMUM RATINGS Absolute-Maximum Values:<br>(T <sub>A</sub> = 25°C unless otherwise specified) |  |                                    |  |   |   |  |  |   |                                     | ELECTRICAL CHARACTERISTICS Typical Values: (T <sub>A</sub> = 25°C unless otherwise specified) |                                    |                                    |  |                                   |        |  |  | MANUFACTURER |
|-------------|------------------------|----------------|--|--|------------------------------------|--|---|---|--|--|---|-------------------------------------|---|------------------------------------|------------------------------------|--|-----------------------------------|--------|--|--|--------------|
|             |                        |                | Reverse Surge Voltage V <sub>R</sub> surge (V)   | Peak Reverse Voltage V <sub>RM</sub> (V) | Reverse Voltage V <sub>R</sub> (V) | Peak Forward Voltage V <sub>FM</sub> (V) | Peak Forward Current I <sub>FM</sub> (mA) | Average Rectified Current I <sub>O</sub> (mA) | Forward Surge Current I <sub>F</sub> surge (A) | Junction Temperature T <sub>J</sub> (°C) | Total Power Dissipation P <sub>D</sub> (mW) | Forward Current I <sub>F</sub> (mA) | Test Condition V <sub>F</sub> (V)   | Forward Voltage V <sub>F</sub> (V) | Test Condition I <sub>F</sub> (mA) | Reverse Current I <sub>R</sub> (μA)              | Test Condition V <sub>R</sub> (V) | Others |  |  |              |
| W02         | Rectifier              | Si-DJ (Bridge) |  |  | 200                                | 200                                      | 1.5A                                      | 50  | 125  |  |   | 1.0                                 | 1.0A  | 10                                 |                                    | R <sub>th</sub> = 50°C/W                         | GENERAL INSTRUMENT                |        |  |  |              |
| 1SS53       | Medium speed switching | Si-EP          |  | 35                                       | 30                                 |  | 300                                       | 100   | 2  | 200                                      | 500   | 0.8                                 | 1.0   | 0.1                                | 30                                 |  | NEC                               |        |  |  |              |
| 1SS55       | Medium speed switching | Si-EP          |  | 100                                      | 75                                 |  | 300                                       | 100   | 2  | 200                                      | 500   | 0.8                                 | 1.0   | 0.1                                | 75                                 |  | NEC                               |        |  |  |              |
| BR -5504S   | Lamp (red)             | GaAlAs         |  |  | 4                                  |  | 300                                       | I <sub>F</sub> = 50                           |  | 85                                       | 100   | 2.0                                 | 20  | 100                                | 4                                  | V <sub>F</sub> = 80 mcd (I <sub>F</sub> = 20 mA) | STANLEY                           |        |  |  |              |

## ZENER DIODES

| DEVICE TYPE | APPLICATIONS | STRUCTURE† | MAXIMUM RATINGS Absolute-Maximum Values:<br>(T <sub>A</sub> = 25°C unless otherwise specified) |                                  |  | ELECTRICAL CHARACTERISTICS Typical Values: (T <sub>A</sub> = 25°C unless otherwise specified) |                                     |  |                                     |   |                                     |                                     |                                    |        |   |    | MANUFACTURER |     |
|-------------|--------------|------------|--|----------------------------------|--|---|-------------------------------------|--|-------------------------------------|---|-------------------------------------|-------------------------------------|------------------------------------|--------|---|----|--------------|-----|
|             |              |            | Total Power Dissipation P <sub>D</sub> (mW)  | Zener Current I <sub>Z</sub> (A) | Junction Temperature T <sub>J</sub> (°C) | Zener Voltage V <sub>Z</sub> (MIN (V), TYP (V), MAX (V))                                      | Test Conditions I <sub>Z</sub> (mA) | Differential Resistance r <sub>Z</sub> (Ω) | Test Conditions I <sub>Z</sub> (mA) | Temperature Coefficient γ <sub>Z</sub> (TYP (mV/°C), MAX (mV/°C)) | Test Conditions I <sub>Z</sub> (mA) | Reverse Current I <sub>Z</sub> (μA) | Test Conditions V <sub>R</sub> (V) | Others |   |    |              |     |
| RD7.5 - EB1 | Regulator    | Si-J       | 400  |                                  | 175                                      | 6.85  | 7.22                                | 20   |                                     | 10  | 20                                  |                                     |                                    |        | 2 | 4  |              | NEC |
| RD15 - EB2  | Regulator    | Si-J       | 400  |                                  | 175                                      | 13.89   | 14.62                               | 10   |                                     | 30  | 10                                  |                                     |                                    |        | 2 | 11 |              | NEC |

**INTEGRATED CIRCUITS  $\mu$ PC741C**

- **Manufacturer:** NEC
- **Applications:** Operational Amplifier

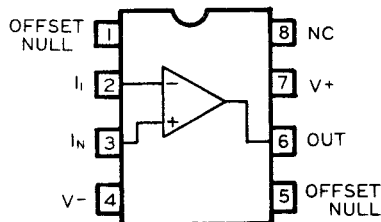
**ABSOLUTE MAXIMUM RATINGS**

|                                      |            |                                       |   |
|--------------------------------------|------------|---------------------------------------|---|
| Supply Voltage . . . . .             | $\pm 18$ V | Input Voltage . . . . .               | $\pm 15$ V                                      |
| Internal Power Dissipation . . . . . | 350 mW     | Storage Temperature Range . . . . .   | $-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ |
| Differential Input Voltage . . . . . | $\pm 30$ V | Operating Temperature Range . . . . . | $-20^{\circ}\text{C}$ to $+75^{\circ}\text{C}$  |

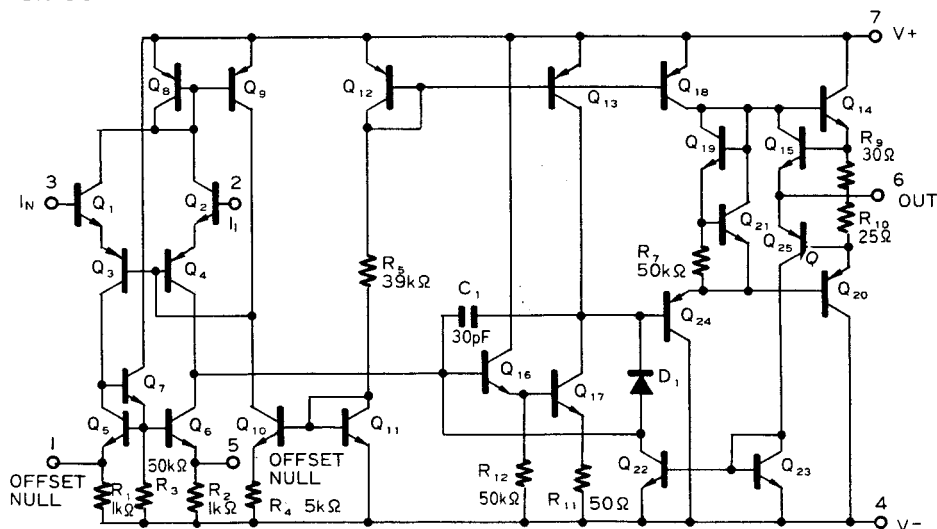
**ELECTRICAL CHARACTERISTICS** ( $V_{CC} = \pm 15\text{V}$ ,  $T_A = +25^{\circ}\text{C}$  unless otherwise noted.)

| PARAMETER                      | CONDITIONS  | MIN | TYP      | MAX | UNITS           |
|--------------------------------|---|-----|----------|-----|-----------------|
| Input Offset Voltage           | $R_S \leq 10\text{ k}\Omega$                              |     | 1.0      | 6.0 | mV              |
| Input Offset Current           |   |     | 20       | 200 | nA              |
| Input Bias Current             |   |     | 80       | 500 | nA              |
| Large-Signal Voltage Gain      | $R_L \geq 2\text{ k}\Omega$<br>$V_{out} = \pm 10\text{V}$ | 106 | 108      |     | dB              |
| Output Voltage Swing           | $R_L \geq 10\text{ k}\Omega$                              | 12  | $\pm 14$ |     | V               |
| Common Mode Rejection Ratio    | $R_S \leq 10\text{ k}\Omega$                              | 70  | 90       |     | dB              |
| Supply Voltage Rejection Ratio | $R_S \leq 10\text{ k}\Omega$                              |     | 30       | 150 | $\mu\text{V/V}$ |
| Power Consumption              |   |     | 45       | 85  | mW              |

**TERMINAL GUIDE (TOP VIEW)**



**EQUIVALENT CIRCUIT**



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